

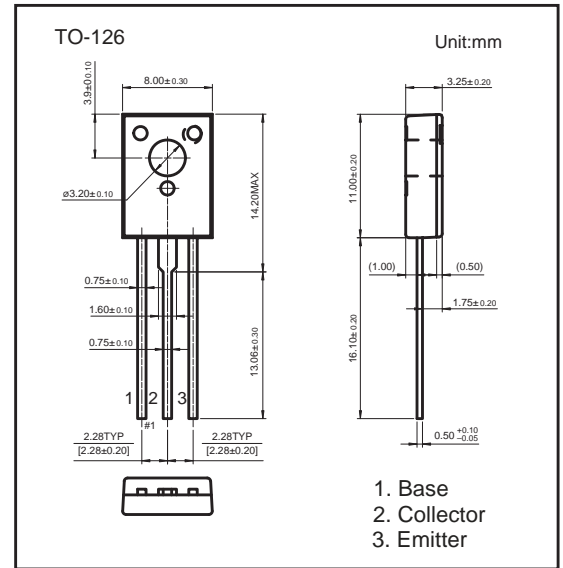
TO-126 Plastic-Encapsulate Transistors

FEATURES

- Excellent hFE linearity and high hFE
- hFE = 60 to 400 (VCE = 2 V, IC = 1 A)
- NPN Transistors

MECHANICAL DATA

- Case style:TO-126 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V _{CB0}	40	V
Collector to Emitter Voltage	V _{CEO}	30	V
Emitter to Base Voltage	V _{EBO}	6	V
Collector Current to Continuous	I _C	3	A
Collector Dissipation	P _c	1	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to 150	°C

PACKAGE INFORMATION

Device	Package	Shipping
2SD882	TO-126	2000/Tape&Reel

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _c =100uA, I _E =0	40			V
Collector-emitter breakdown voltage	V _{CEO}	I _C = 10 mA, I _B =0	30			V
Emitter-base breakdown voltage	V _{EBO}	I _E = 100 uA, I _C =0	6			V
Collector cut-off current	I _{CB0}	V _{CB} =40 V, I _E =0			1	uA
Collector cut-off current	I _{CEO}	V _{CE} =30 V, I _B =0			10	uA
Emitter cut-off current	I _{EBO}	V _{EB} =6V, I _C =0			1	uA
DC current gain	h _{FE}	V _{CE} = 2V, I _C = 1A	60		400	
		V _{CE} =2V, I _C = 100mA	32			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =2A, I _B = 0.2A			0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =2A, I _B = 0.2A			1.5	V
Transition frequency	f _T	V _{CE} =5 V, I _C =0.1mA, f = 10MHz	50			MHz

Classification of h_{FE}(1)

Type	2SD882-R	2SD882-Q	2SD882-P	2SD882-E
Range	60-120	100-200	160-320	200-400